SKN 2F50



Stud Diode

Fast Recovery Rectifier Diode

SKN 2F50

Features

- Small recovered charge
- Soft recovery
- Up to 1000 V reverse voltage
- Hermetic metal case with glass
 insulator
- Threaded stud ISO M6 or 1/4-28
 UNF
- SKN: anode to stud

Typical Applications

- Inverse diodes for power transistors, GTO thyristors, asymmetric thyristors
- SMPS, inverters, choppers
- For severe ambient conditions

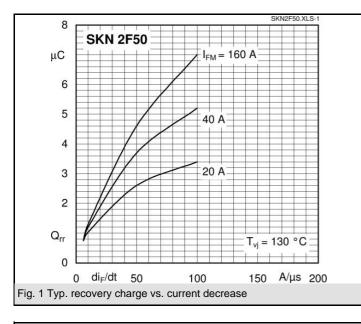
14	14			
V _{RSM}	V _{RRM}	I _{FRMS} = 100 A (maximum value for continuous operation)		
V	V	I _{FAV} = 50 A (sin. 180; 5000 Hz; T _c = 105 °C)		
400	400	SKN 2F50/04		
400	400	SKN 2F50/04UNF		
600	600	SKN 2F50/06		
600	600	SKN 2F50/06UNF		
800	800	SKN 2F50/08		
800	800	SKN 2F50/08UNF		
1000	1000	SKN 2F50/10		
1000	1000	SKN 2F50/10UNF		

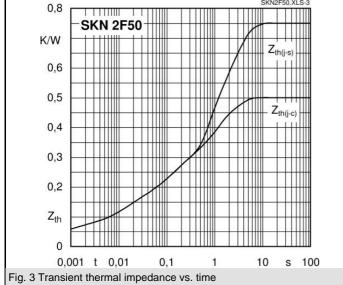
Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 85 (100) °C	69 (57)	А
I _{FAV}	K3; T _a = 45 °C; sin. 180; 5000 Hz	18	
I _{FSM}	T _{vi} = 25 °C; 10 ms	1100	A
	T _{vi} = 150 °C; 10 ms	940	А
i²t	T _{vj} = 25 °C; 8,3 10 ms	6000	A²s
	T _{vj} = 150 °C; 8,3 10 ms	4400	A²s
V _F	T _{vi} = 25 °C; I _F = 50 A	max. 1,8	V
V _(TO)	T _{vi} = 150 °C	max. 1,2	V
r _T	T _{vi} = 150 °C	max. 4	mΩ
I _{RD}	$T_{vj} = 25 \text{ °C}; V_{RD} = V_{RRM}$	max. 0,4	mA
I _{RD}	T _{vj} = 130 °C; V _{RD} = V _{RRM}	max. 50	mA
Q _{rr}	T _{vi} = 130 °C, I _F = 100 A,	3	μC
I _{RM}	-di/dt = 30 A/µs, V _R = 30 V	10	А
t _{rr}		600	ns
E _{rr}		-	mJ
R _{th(j-c)}		0,5	K/W
R _{th(c-s)}		0,25	K/W
T _{vj}		- 40 + 150	°C
T _{stg}		- 55 + 150	°C
V _{isol}		-	٧~
Ms	to heatsink	2,5	Nm
a		5 * 9,81	m/s²
m	approx.	20	g
Case		E 10	

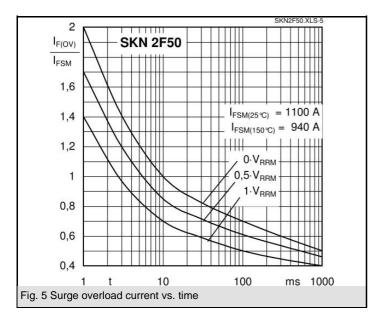


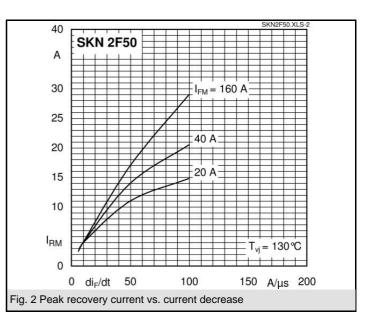
SKN

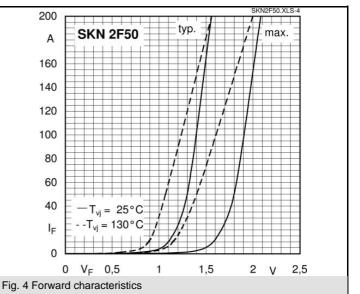
SKN 2F50



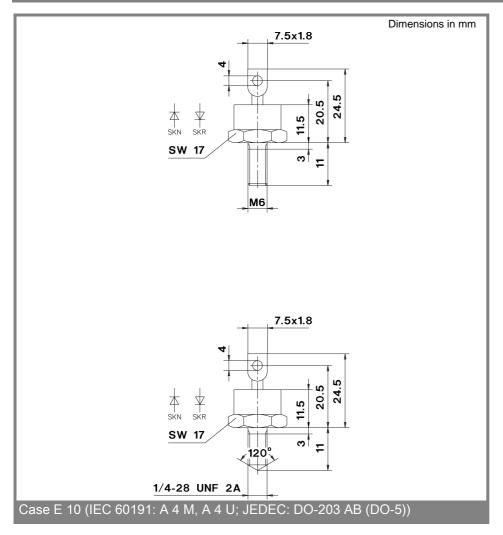








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